

Docket No.: P2001,0176

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on the date indicated below.

By: 

Date: October 1, 2003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No. : 10/657,841
Applicant : Johannes Baur et al.
Filed : September 9, 2003
Art Unit : to be assigned
Examiner : to be assigned

Docket No. : P2001,0176
Customer No. : 24131

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner for Patents

Sir:

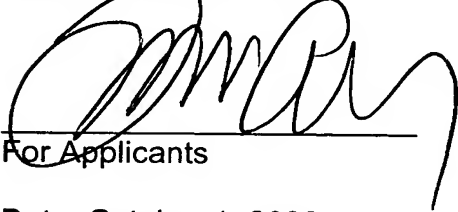
In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

Japanese Patent Abstract JP 61 110 476 (Yanagihara), dated May 28, 1986;

J. Zhang et al.: "Precise microfabrication of wide band gap semiconductors (SiC and GaN) by VUV-UV multiwavelength laser ablation", *Applied Surface Science*, Vol. 127-129, 1998, pp. 793-799;

W. N. Carr: "Photometric Figures Of Merit For Semiconductor Luminescent Sources Operating in Spontaneous Mode", *Infrared Physics*, 1966, Vol. 6, pp. 1-19.

Respectfully submitted,



For Applicants

LAURENCE A. GREENBERG
REG. NO. 29,308

Date: October 1, 2003

Lerner And Greenberg, P.A.
Post Office Box 2480
Hollywood, FL 33022-2480
Tel: (954) 925-1100
Fax: (954) 925-1101

/bmb

FORM PTO-1449 (SUBSTITUTE)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

Attorney Docket No.:

P2001,0176

Applic. No.

10/657,841

Applicant

Johannes Baur et al.

Filing Date

September 9, 2003

Group Art Unit

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(37 CFR 1.98(b))

U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A						
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J	61 110 476	05/28/86	Japan			X
	K						
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

O	J. Zhang et al.: "Precise microfabrication of wide band gap semiconductors (SiC and GaN) by VUV-UV multiwavelength laser ablation", <i>Applied Surface Science</i> , Vol. 127-129, 1998, pp. 793-799
P	W. N. Carr: "Photometric Figures Of Merit For Semiconductor Luminescent Sources Operating in Spontaneous Mode", <i>Infrared Physics</i> , 1966, Vol. 6, pp. 1-19

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

